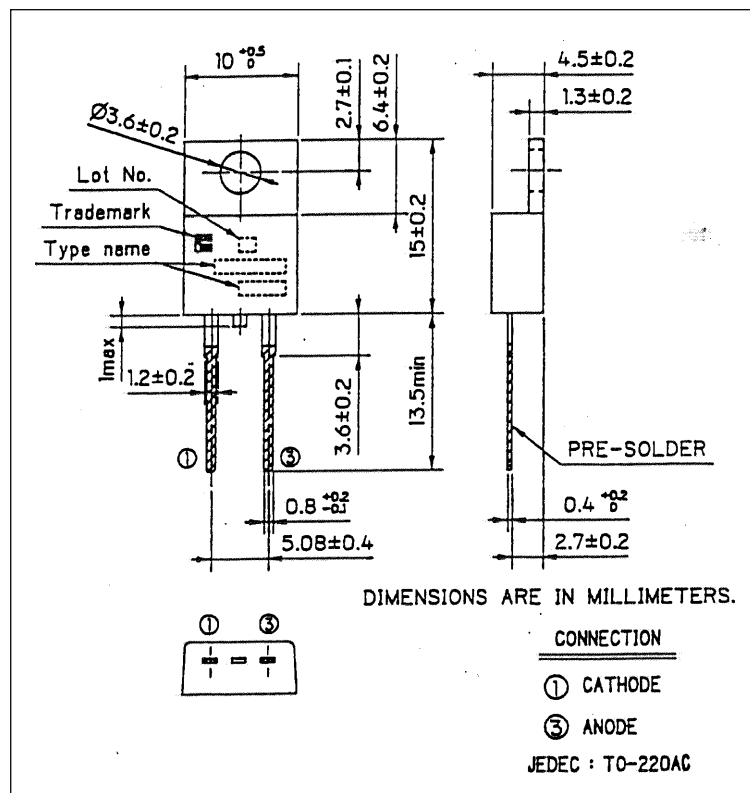
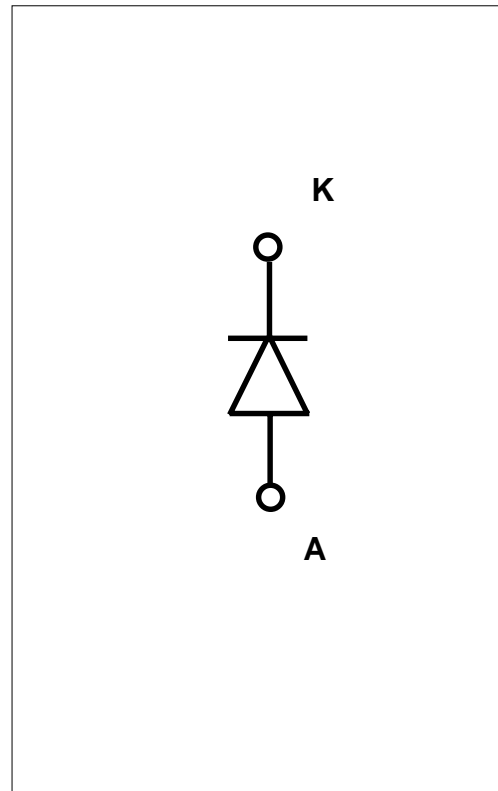


## Fast Recovery Diode for IGBT

### Outline Drawings Units mm



### Equivalent circuit



### Maximum ratings and characteristics

#### Absolute maximum ratings (Tc=25°C)

Item	Symbol	Test Conditions	Ratings	Units	
Repetitive Reverse Voltage	VRRM		1200	V	
Repetitive peak surge current	IFM	20kHz Duty 50% Squ. wave	Tc=124°C	8	A
			Tc=25°C	26	A
Average rectified forward current	IF(A)	DC	8	A	
Non-repetitive peak surge current	IFSM	Pulse 10ms, sin. wave	72	A	
Maximum Power Dissipation	Po		50	W	
Operating Temperature	Tj		+150	°C	
Storage Temperature	Tstg		-40 to +150	°C	
Mounting Screw Torque			50	N-cm	

#### Electrical characteristics (at Tc=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	IR	VR = 1200V	1.0	mA
Forward voltage	VFM	IF = 8A	3.0	V
Reverse recovery time	trr	IF = 8A, VR=200V, di/dt=100A/μs	0.3	μs

#### Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	Rth(j-c)	junction to case	2.50	°C/W

Characteristics

